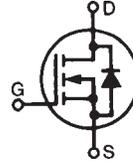


# Polar2™ HiperFET™ Power MOSFET

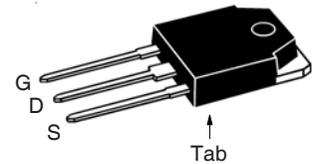
## IXFQ24N50P2

$V_{DSS} = 500V$   
 $I_{D25} = 24A$   
 $R_{DS(on)} \leq 270m\Omega$

N-Channel Enhancement Mode  
 Avalanche Rated  
 Fast Intrinsic Diode



TO-3P



G = Gate      D = Drain  
 S = Source    Tab = Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $150^\circ C$	500	V
$V_{DGR}$	$T_J = 25^\circ C$ to $150^\circ C$ , $R_{GS} = 1M\Omega$	500	V
$V_{GSS}$	Continuous	$\pm 30$	V
$V_{GSM}$	Transient	$\pm 40$	V
$I_{D25}$	$T_C = 25^\circ C$	24	A
$I_{DM}$	$T_C = 25^\circ C$ , Pulse Width Limited by $T_{JM}$	50	A
$I_A$	$T_C = 25^\circ C$	12	A
$E_{AS}$	$T_C = 25^\circ C$	750	mJ
$dv/dt$	$I_S \leq I_{DM}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ C$	15	V/ns
$P_D$	$T_C = 25^\circ C$	480	W
$T_J$		-55 ... +150	$^\circ C$
$T_{JM}$		150	$^\circ C$
$T_{stg}$		-55 ... +150	$^\circ C$
$T_L$	Maximum Lead Temperature for Soldering	300	$^\circ C$
$T_{SOLD}$	Plastic Body for 10s	260	$^\circ C$
$M_d$	Mounting Torque	1.13/10	Nm/lb.in.
<b>Weight</b>		5.5	g

### Features

- Fast Intrinsic Diode
- Dynamic  $dv/dt$  Rating
- Avalanche Rated
- Low  $R_{DS(ON)}$  and  $Q_G$
- Low Package Inductance

### Advantages

- High Power Density
- Easy to Mount
- Space Savings

### Applications

- Switch-Mode and Resonant-Mode Power Supplies
- DC-DC Converters
- Battery Chargers
- Uninterrupted Power Supplies
- AC and DC Motor Drives
- High Speed Power Switching Application

Symbol	Test Conditions ( $T_J = 25^\circ C$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	500		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	2.5		4.5 V
$I_{GSS}$	$V_{GS} = \pm 30V$ , $V_{DS} = 0V$			$\pm 100$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$ $T_J = 125^\circ C$			25 $\mu A$ 1 mA
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 0.5 \cdot I_{D25}$ , Note 1			270 m $\Omega$

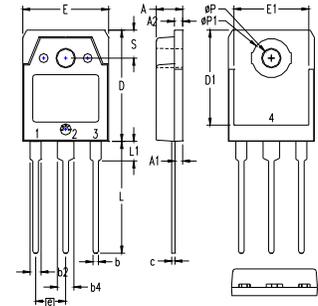
Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{V}, I_D = 0.5 \cdot I_{D25}$ , Note 1	14	24	S
$C_{iss}$	$V_{GS} = 0\text{V}, V_{DS} = 25\text{V}, f = 1\text{MHz}$		2890	pF
$C_{oss}$			280	pF
$C_{rss}$			22	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$ $R_G = 10\Omega$ (External)		15	ns
$t_r$			9	ns
$t_{d(off)}$			30	ns
$t_f$			5	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 \cdot I_{D25}$		48	nC
$Q_{gs}$			13	nC
$Q_{gd}$			16	nC
$R_{thJC}$				$0.26^\circ\text{C/W}$
$R_{thCS}$		0.25		$^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			24 A
$I_{SM}$	Repetitive, Pulse Width Limited by $T_{JM}$			96 A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{V}$ , Note 1			1.3 V
$t_{rr}$	$I_F = 12\text{A}, -di/dt = 100\text{A}/\mu\text{s}$ $V_R = 100\text{V}, V_{GS} = 0\text{V}$			200 ns
$I_{RM}$			10	A
$Q_{RM}$			0.69	$\mu\text{C}$

Note 1. Pulse test,  $t \leq 300\mu\text{s}$ , duty cycle,  $d \leq 2\%$ .

### TO-3P (IXFQ) Outline

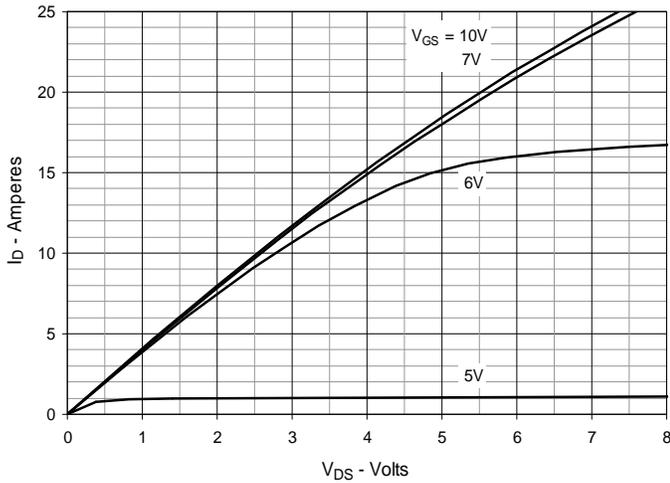
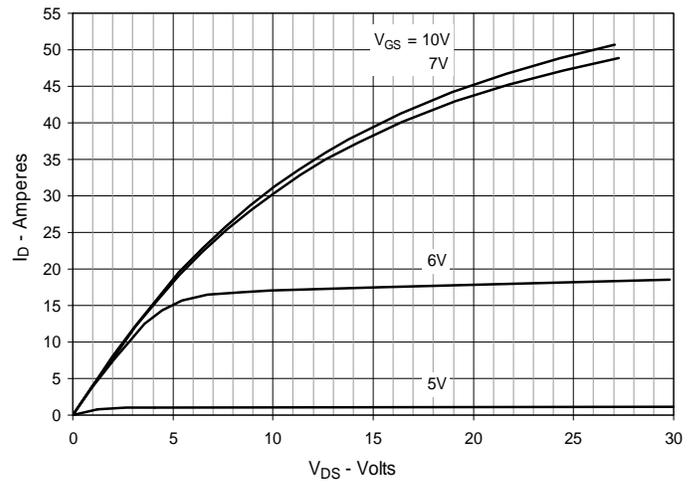
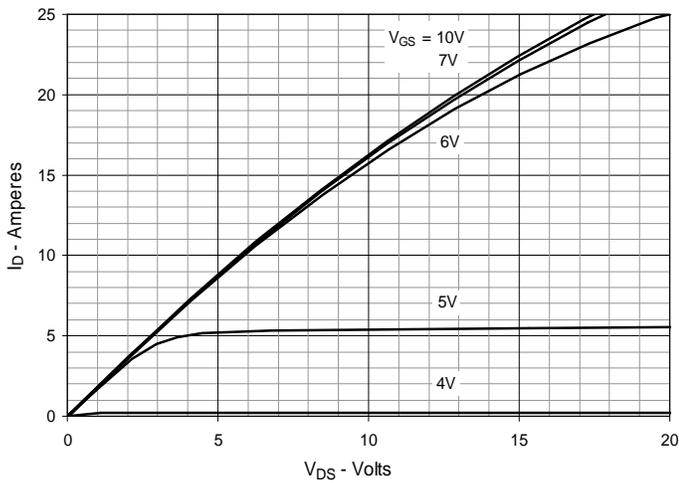
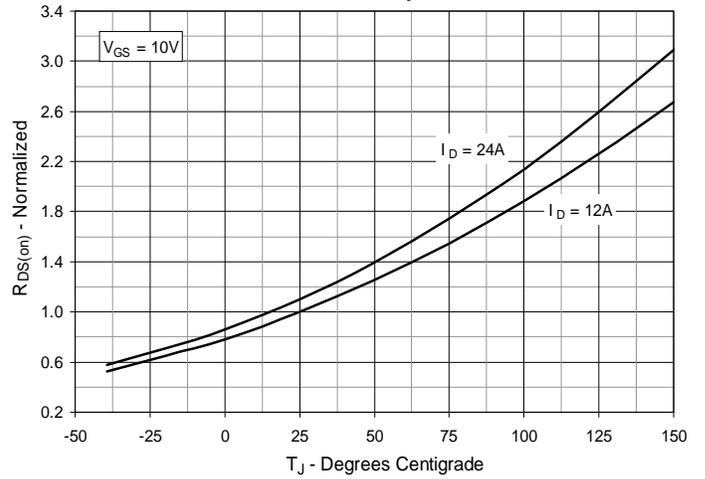
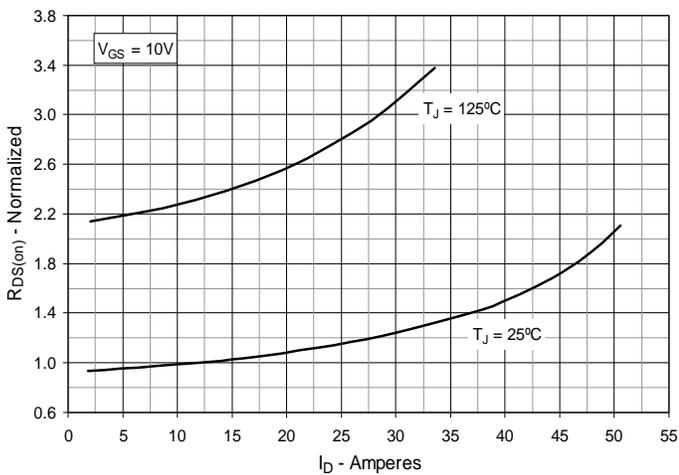
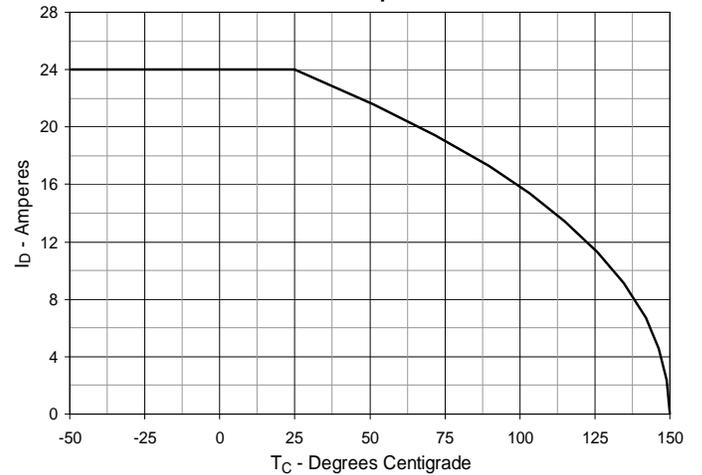


- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - DRAIN (COLLECTOR)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.185	.193	4.70	4.90
A1	.051	.059	1.30	1.50
A2	.057	.065	1.45	1.65
b	.035	.045	0.90	1.15
b2	.075	.087	1.90	2.20
b4	.114	.126	2.90	3.20
c	.022	.031	0.55	0.80
D	.780	.799	19.80	20.30
D1	.665	.677	16.90	17.20
E	.610	.622	15.50	15.80
E1	.531	.539	13.50	13.70
e	.215 BSC		5.45 BSC	
L	.779	.795	19.80	20.20
L1	.134	.142	3.40	3.60
$\phi P$	.126	.134	3.20	3.40
$\phi P1$	.272	.280	6.90	7.10
S	.193	.201	4.90	5.10

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$** 

**Fig. 3. Output Characteristics @  $T_J = 125^\circ\text{C}$** 

**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 12\text{A}$  Value vs. Junction Temperature**

**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 12\text{A}$  Value vs. Drain Current**

**Fig. 6. Maximum Drain Current vs. Case Temperature**


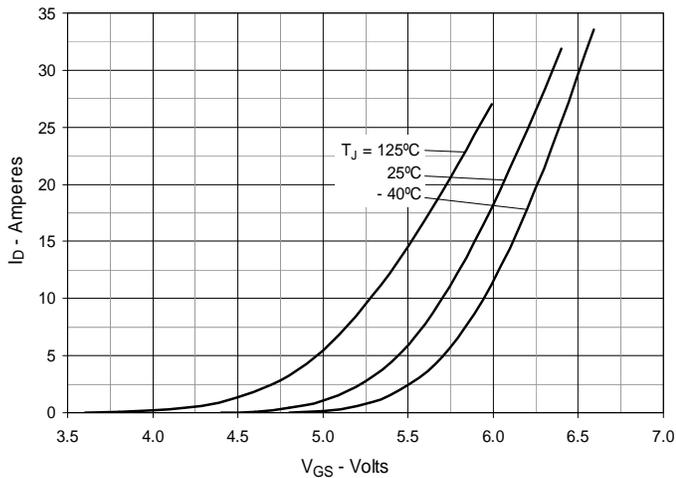
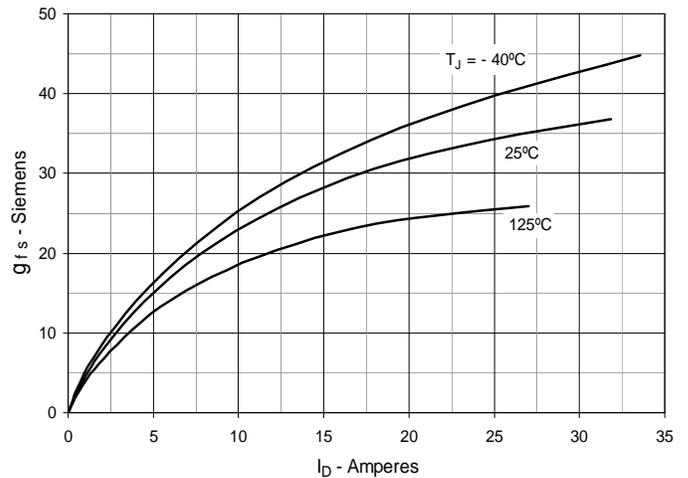
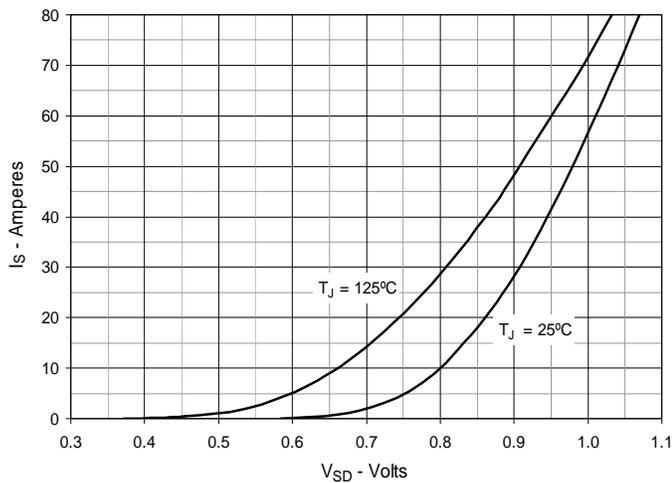
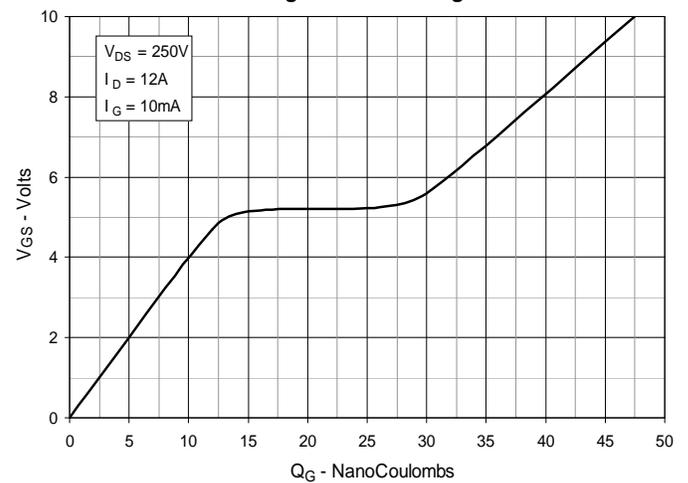
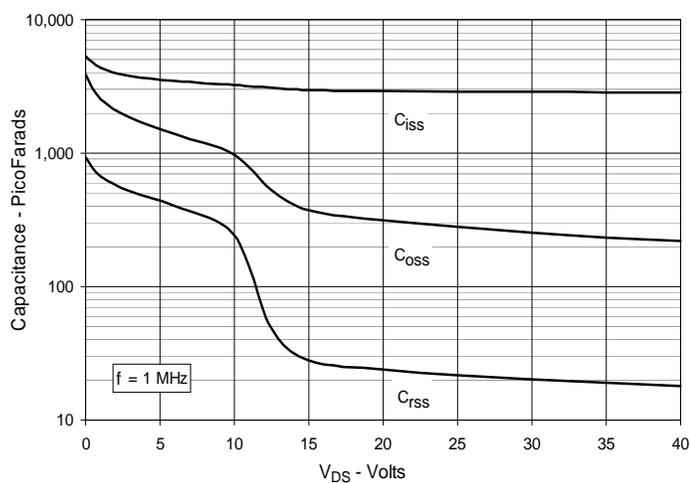
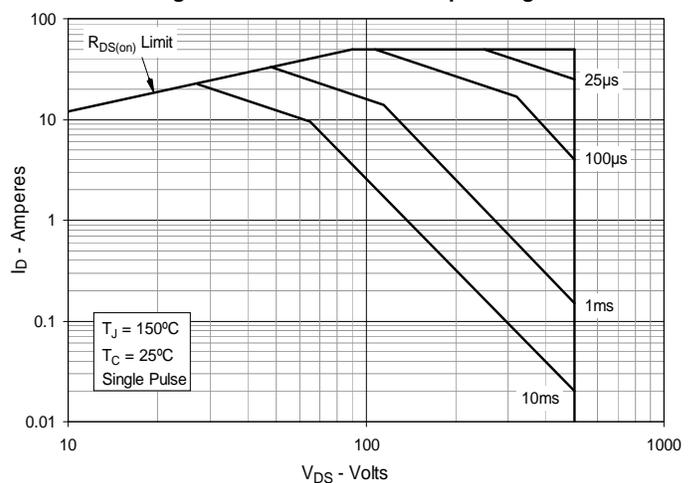
**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Forward-Bias Safe Operating Area**


Fig. 13. Maximum Transient Thermal Impedance

